

Large-signal Power MOSFETs (4)

The Sanyo J-MOS series utilizes Sanyo's own fine fabrication process for power devices to develop an entire series of ultrahigh performance power devices capable of high voltage, high speed and large current operation.

With performance of wide applications for virtually any types of power electronic equipment, the UH Series, AP Series and LD Series offer the most suitable devices to meet specific needs.

In addition to the below SANYO has a wide variety of package of small-signal power MOSFET series. See the tables on other pages.

dc AP Series (Advanced Performance)

The AP Series provides an on-state resistance approximately 40% lower than the existing J-MOS series. A precisely controlled, channel forming process is used to achieve a threshold value variation width of 0.5V resulting in easy parallel connection operation essential for large current circuits. (VGS=30V guaranteed in VDSS 450V series.) Designed as a power MOSFET with well-balanced characteristics, the AP Series provides the ultimate in high-power performance. The surface mounting TP, SMP and ZP package enables higher density assembly and higher reliability.

Applications *Battery charger, Ac adapter, motor control, inverter lighting, switching power supply, AV equipment etc.

VDSS 400V system

Type No. *:FRD built in	Package	Absolute Maximum Ratings /Ta=25°C					Electrical Characteristics/Ta=25°C				Type No. *:FRD built in
		V _{DSS} (V)	V _{GSS} (V)	I _D (A)	I _{DP} (A)	P _D (W)	V _{GS} (off) min ~ max (V)	R _{DS(on)} typ (Ω)	C _{iss} typ (PF)		
2SJ522*	SMP			5	20	70	2~3	1.5/2	1500	2SJ522*	
2SK3092	TP			3	12	30	3~4	*1.8/2.3	360	2SK3092	
2SK3093	TO-220CI	400	±30	3	12	20	3~4	*1.8/2.3	360	2SK3093	
2SK3095				5	20	25		*0.92/1.2	660	2SK3095	
2SK3097				6.5	26	30		*0.68/0.87	860	2SK3097	
2SK3099				9	36	35		*0.43/0.55	1150	2SK3099	
2SK3101				11	44	40		*0.32/0.4	1850	2SK3101	
2SK3094	TO-220	400	±30	5.5	22	55	3~4	*0.92/1.2	660	2SK3094	
2SK3096				7	28	70		*0.68/0.87	860	2SK3096	
2SK3098				12	48	85		*0.43/0.55	1150	2SK3098	
2SK3100				16	64	90		*0.32/0.4	1850	2SK3100	

VDSS 450V system

2SJ457*	TP			0.5	2	30		11/15	300	2SJ457*	
2SK2406*				1	4	30		3.5/4.5	300	2SK2406*	
2SK2434				5	20	40		1/1.4	700	2SK2434	
2SJ458*				2	8	60		4/5.5	700	2SJ458*	
2SJ459*				4	16	70		2/2.8	1500	2SJ459*	
2SK1690	SMP			3	12	50		2/2.6	400	2SK1690	
2SK1691				5	20	60		1/1.4	700	2SK1691	
2SK2403*				3	12	50		2.4/3.2	380	2SK2403*	
2SK2404*				5	20	60		1.2/1.6	700	2SK2404*	
2SK2405*				10	40	70		0.55/0.75	1500	2SK2405*	
2SK1438	TO-220			0.3	1.2	20	2~3	9/12	90	2SK1438	
2SK1439				3	12	50		2/2.6	400	2SK1439	
2SK1440				5	20	60		1/1.4	700	2SK1440	
2SK1441				8	32	70		0.6/0.8	1200	2SK1441	
2SK1442				12	48	70		0.47/0.6	1600	2SK1442	
2SK2407*				10	40	70		0.55/0.75	1500	2SK2407*	
2SK1443LS	TO-220FI(LS)			1	4	20		3.5/4.5	250	2SK1443LS	
2SK1444LS				3	12	25		2/2.6	400	2SK1444LS	
2SK1445LS				5	20	30		1/1.4	700	2SK1445LS	
2SK1446LS				7	28	35		0.6/0.8	1200	2SK1446LS	
2SK1447LS				9	36	40		0.47/0.6	1600	2SK1447LS	
2SK2787LS*				8	32	40		0.55/0.75	1500	2SK2787LS*	
2SK1448	TO-3PB			8	32	100		0.6/0.8	1200	2SK1448	
2SK1449				12	48	120		0.47/0.6	1600	2SK1449	
2SK1450				20	80	150		0.24/0.3	3200	2SK1450	
2SK1451	TO-3PML			8	32	50		0.6/0.8	1200	2SK1451	
2SK1452				10	40	60		0.47/0.6	1600	2SK1452	
2SK1453				16	64	70		0.24/0.3	3200	2SK1453	
2SK1454	TO-3PBL			30	120	250		0.12/0.16	6400	2SK1454*	

VDSS 500V system (H-III Series)

2SK2616	TP	500	±30	2	8	30	3.5~5.5	*3/4	300	2SK2616	
2SK2619	SMP			6	24	70		*0.95/1.25	700	2SK2619	
2SK2617LS	TO-220FI(LS)			4	16	25		*1.2/1.6	550	2SK2617LS	
2SK2618LS				5	20	30		*0.95/1.25	700	2SK2618LS	

Underlined type Nos. are before mass production.

Precaution Take care to prevent device breakage from static electricity because MOSFETs cannot withstand much static electricity.

These specifications are subject to change without notice.

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